Diode Semiconductor Device - Page 1 of 1



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Inc	Iosure Material:
Gla	iss and metal
Ov	erall Length:
0.3	40 inches
Ov	erall Diameter:
0.1	87 inches
Мо	unting Facility Quantity:
1	
Мо	unting Method:
Thr	readed stud
Fea	atures Provided:
He	rmetically sealed case
Th	read Size:
0.1	12 inches
Sei	miconductor Material:
Sili	con
Vo	tage Rating In Volts Per Characteristic:
70.	0 regulator voltage
Cu	rrent Rating Per Characteristic:
3.3	0 amperes forward current, average absolute
Po	wer Rating Per Characteristic:
10.	0 watts small-signal input power, common-collector preset
Ма	ximum Operating Tempurature Per Measurement Point:
175	5.0 degrees celsius ambient air
Th	read Series Designator:
Un	C
Ter	minal Type And Quantity:
1 th	nreaded stud and 1 turret
Sh	elf Life:
N/a	l de la construcción de la constru
Un	it Of Measure:
De	militarization:
No	
Fiig	g:
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